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[Continued on next page]

(54) Title: SEMICONDUCTOR SUBSTRATE SURFACE PREPARATION METHOD

(57) Abstract: The invention relates to a method for preparing a surface of a semiconductor substrate comprising the steps of oxidizing the surface of the semiconductor substrate to thereby transform the natural oxide into an artificial oxide and of removing the artificial oxide, in particular to obtain an oxide-free substrate surface.

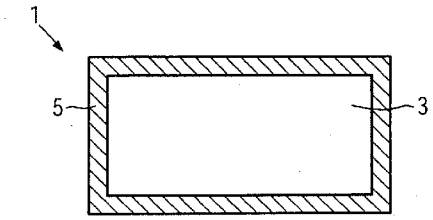


FIG. 1a

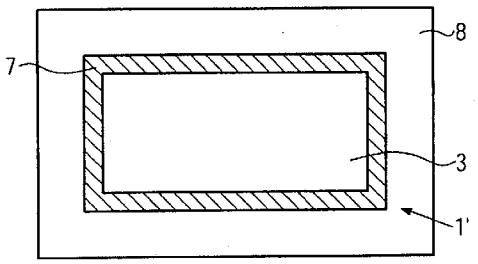


FIG. 1b

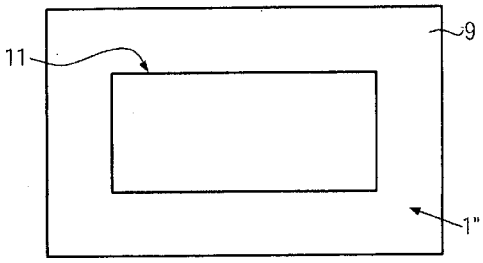


FIG. 1c

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